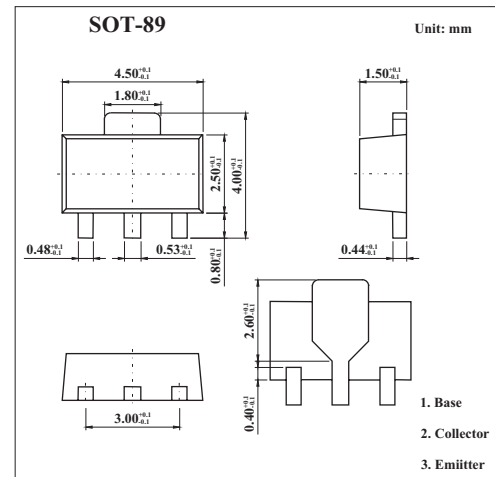


Power Transistor

2SA1797

■ Features

- Low saturation voltage. $V_{CE(sat)} = -0.35V(\text{Max.})$ at $I_C / I_B = -1A / -50mA$.
- Excellent DC current gain characteristics.
- Complements the 2SA1797 and 2SC4672.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-emitter Voltage	V_{CEO}	-50	V
Collector-base Voltage	V_{CBO}	-50	V
Emitter-base Voltage	V_{EBO}	-6	V
Collector current	I_C	-3	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = -1mA$	-50			V
Collector-base breakdown voltage	BV_{CBO}	$I_C = -50 \mu A$	-50			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50 \mu A$	-6			V
Collector cutoff current	I_{CBO}	$V_{CB} = -50V$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V$			-0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$		-0.15	-0.35	V
DC current transfer ratio	h_{FE}	$V_{CE} = -2V, I_C = -0.5A$	82		270	
Transition frequency	f_T	$V_{CE} = -2V, I_E = 0.5A, f = 100MHz$		200		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		36		pF

■ hFE Classification

Marking	AG	
	P	Q
hFE	82~180	120~270